



2822

THE UNITED STATES PATENT AND TRADEMARK OFFICE

RECEIVED
FEB - 5 2002
TECHNOLOGY CENTER 2800
#14/C
Huan
2602

In re application of

MANABU TOMITA ET AL.

Serial No. 09/387,477 (TIJ-26105)

Filed September 1, 1999

For: SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD THEREOF

Art Unit 2822

Examiner M. Guerrero

Commissioner for Patents
Washington, D. C. 20231

Sir:

AMENDMENT UNDER 37 C.F.R. 1.111

In response to the Office action dated October 25, 2001, please amend the above-identified application as follows:

In the claims:

Amend claim 1 as follows:

1. (Twice Amended) A [S]semiconductor device manufacturing method comprising the steps of:

providing a semiconductor substrate having a lower electrically conducting layer thereon and an electrically insulating layer [formed thereon] disposed over said electrically conducting layer;

providing a gas etchant comprising a mixed gas of multiple different fluorocarbon gases, each fluorocarbon gas having a different ratio of carbon atoms to fluorine atoms, the